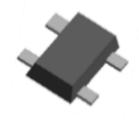


Features :

 Low noise figure and high associated gain NF=0.35dB TYP., Ga=14.1dB TYP.
 @VDS=2V, ID=10mA, f=12GHz

Description :

- Super Low Noise and High Gain.
- Original Dual mold Plastic package.



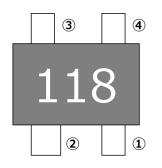
Applications :

• Ku-band LNB (Low Noise Block)

Package :

• Flat-lead 4-pin thin-type super minimold package

PIN Configuration :



PIN No.	PIN Name
1	Source
2	Drain
3	Source
4	Gate

Ordering Information :

Part Number	Order Number	Package	Marking	Supplying Form
CKRF7613MM34-C2	CKRF7613MM34-C2	Flat-lead 4-pin	118	•Embossed 8 mm wide
		thin-type super		•Pin 1 (Source), Pin 2 (Drain)
		minimold package		Face the perforation side of the
				Таре
				•Qty 15Kpcs/reel



Absolute Maximum Ratings :

Parameter	Symbol	Rating	Unit		
Drain to Source Voltage	VDS	4.0	V		
Gate to Source Voltage	VGS	-2.4	V		
Drain Current	ID	IDSS	mA		
Gate Current	IG	80	μA		
Total Power Dissipation	Ptot	125	mW		
Channel Temperature	Tch	+150	°C		
Storage Temperature	Tstg	-55 to +125	°C		
Operation temperature	Тор	-55 to +125	°C		

Recommended Operating Range :

(TA=+25℃, unless otherwise specified)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	VDS	+1	+2	+3	V
Drain Current (ID constant circuit)	ID	5	10	15	mA

Electrical Characteristics :

(TA=+25℃, unless otherwise specified)

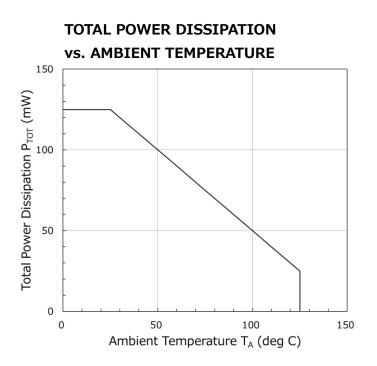
Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Gate to Source Leak Current	IGSO	VGS=-3.0V	-	0.30	10.0	μA
Saturated Drain Current	IDSS	VDS=2V, VGS=0V	6.3	20.0	31.9	mA
Gate to Source Cut-off Voltage	VGS(off)	VDS=2V, ID=120µA	-0.67	-0.40	-0.10	V
Trans conductance	Gm	VDS=2V, ID=10mA	51.8	73.4	-	mS
Noise Figure	NF	VDS=2V, ID=10mA,	-	0.35	0.53	dB
Associated Gain	Ga	f=12GHz	12.4	14.1	-	dB

12GHz Low Noise FET in Dual mold Plastic PKG



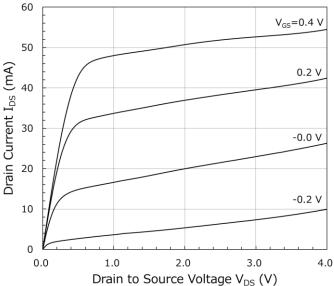
TYPICAL CHARACTERISTICS:

 $(TA=+25^{\circ}C, unless otherwise specified)$



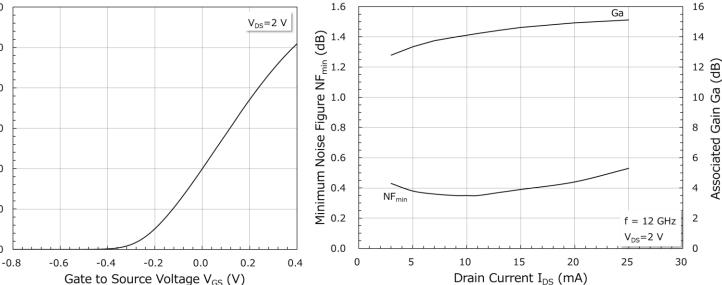
DRAIN CURRENT vs.

DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



GATE TO SOURCE VOLTAGE 60 1.6 V_{DS}=2 V 50 Drain Current I_{DS} (mA) 40

MINIMUM NOISE FIGURE & ASSOCIATED GAIN vs. DRAIN CURRENT



CDS-0069-02

30

20

10

0

12GHz Low Noise FET in Dual mold Plastic PKG

S-Parameters :

S-parameters/Noise parameters are provided on the CDK Web site. [Original Products] \rightarrow [Low Noise GaAsFET for LNB] \rightarrow [Device Parameters] URL http://www.en.cdk.co.jp/products/highfrequency/rf/LNGaAsFET/LNB/index.html

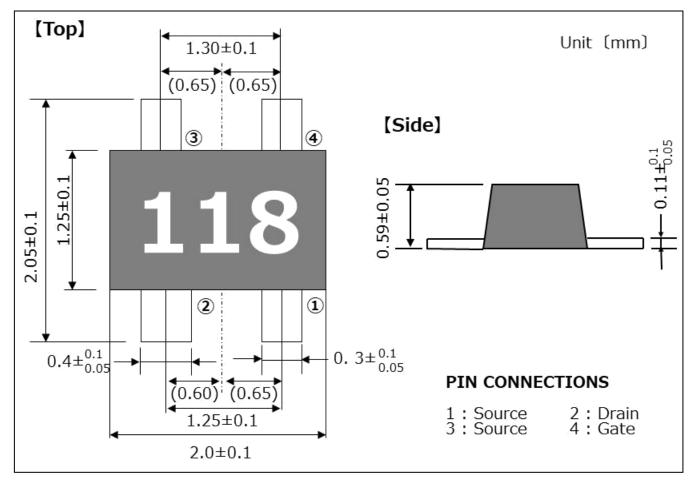
RF Measuring Layout Pattern :

RF Measuring Layout Patterns are provided on the CDK Web site.

 $[\texttt{Original Products}] \rightarrow [\texttt{Low Noise GaAsFET for LNB}] \rightarrow [\texttt{Design Support}] \rightarrow$

[Evaluation Board Information]

URL http://www.en.cdk.co.jp/products/highfrequency/rf/LNGaAsFET/LNB/designsupport/index.html



Package Dimensions :



12GHz Low Noise FET in Dual mold Plastic PKG



Recommended Soldering Conditions :

Recommended Soldering Conditions are provided on the CDK Web site. [Original Products] \rightarrow [Low Noise GaAsFET for LNB] \rightarrow [Design Support] \rightarrow [others] URL <u>http://www.en.cdk.co.jp/products/highfrequency/rf/LNGaAsFET/LNB/designsupport/index.html</u>

12GHz Low Noise FET in Dual mold Plastic PKG



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12GHz Low Noise FET in Dual mold Plastic PKG



[Caution in the gallium arsenide (GaAs) product handling]

This product uses gallium arsenide (GaAs) of the toxic substance appointed in laws and ordinances. GaAs vapor and powder are hazardous to human health if inhaled or ingested.

- $\boldsymbol{\cdot}$ Do not dispose in fire or break up this product.
- \cdot Do not chemically make gas or powder with this product.
- When discard this product, please obey the law of your country.
- Do not lick the product or in any way allow it to enter the mouth.

[CAUTION]

Although this device is designed to be as robust as possible, ESD (Electrostatic Discharge) can damage this device. This device must be protected at all times from ESD. Static charges may easily produce potentials of several kilovolts on the human body or equipment, which can discharge without detection. Industry-standard ESD precautions should be used at all times.

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